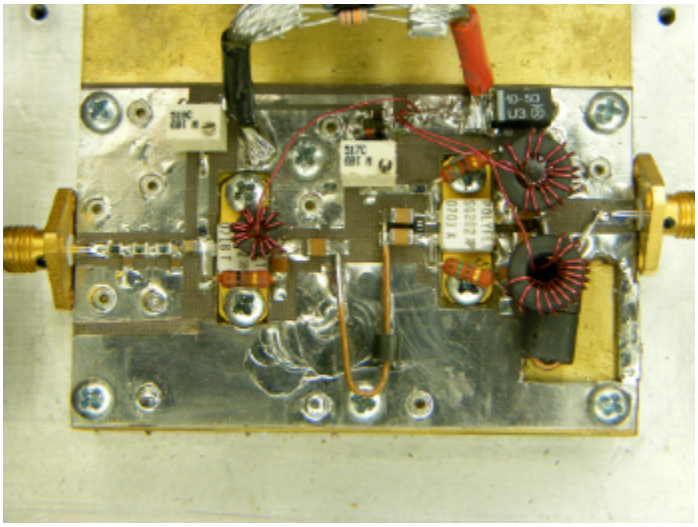
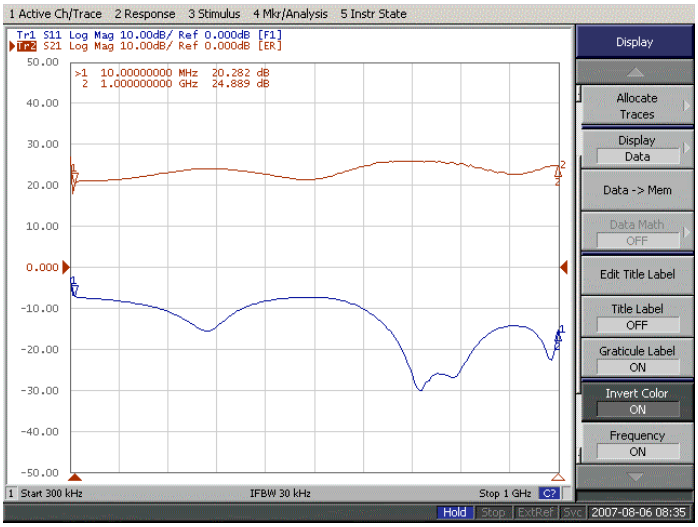
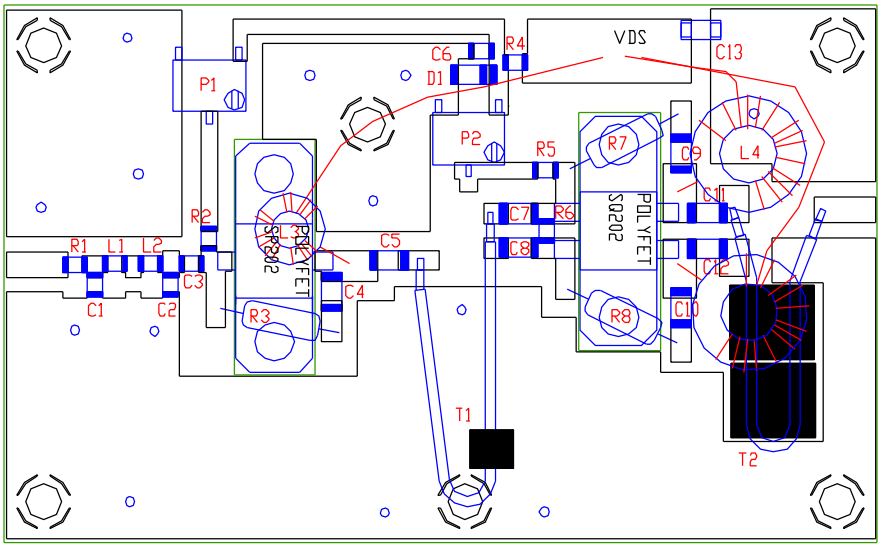






SYMBOL	VALUE	DESCRIPTION
C1	6pF	0805 chip cap
C2	8pF	0805 chip cap
C3	100nF	0805 chip cap
C4, C9, C10	10nF	ATC-200B Chip Cap
C5, C7, C8, C11, C12	100nF	ATC-200B Chip Cap
C6	10nF	0805 chip cap
C13	10uF	50V tantalum
D1	5.6V	Zener Diode
R1	10.2	0805 chip resistor
R2, R5	9.1k	0805 chip resistor
R3	100	1 Watt Axial
R4	3.9k	0805 chip resistor
R6	180	0805 chip resistor
R7, R8	150	1 Watt Axial
P1, P2	10k	6mm multi-turn pot
L1, L2	1.8nH	0805 chip inductor
L3	24AWG	15x, 1 of FT-23-43
L4, L5	24AWG	14x, 1 of FT-37-43
Q1	SP202	Polyfet Transistor
Q2	SQ202	Polyfet Transistor
T1	2"	UT34-10, 1 of FB-43-101
T2	1.8"	UT34-25, 2 of BN-61-2402
Vdd	28V	Drain Voltage
Bias	0.8A	0.4A+0.4A

PCB= Teflon, er=2.55, 1oz, thickness = 30mil

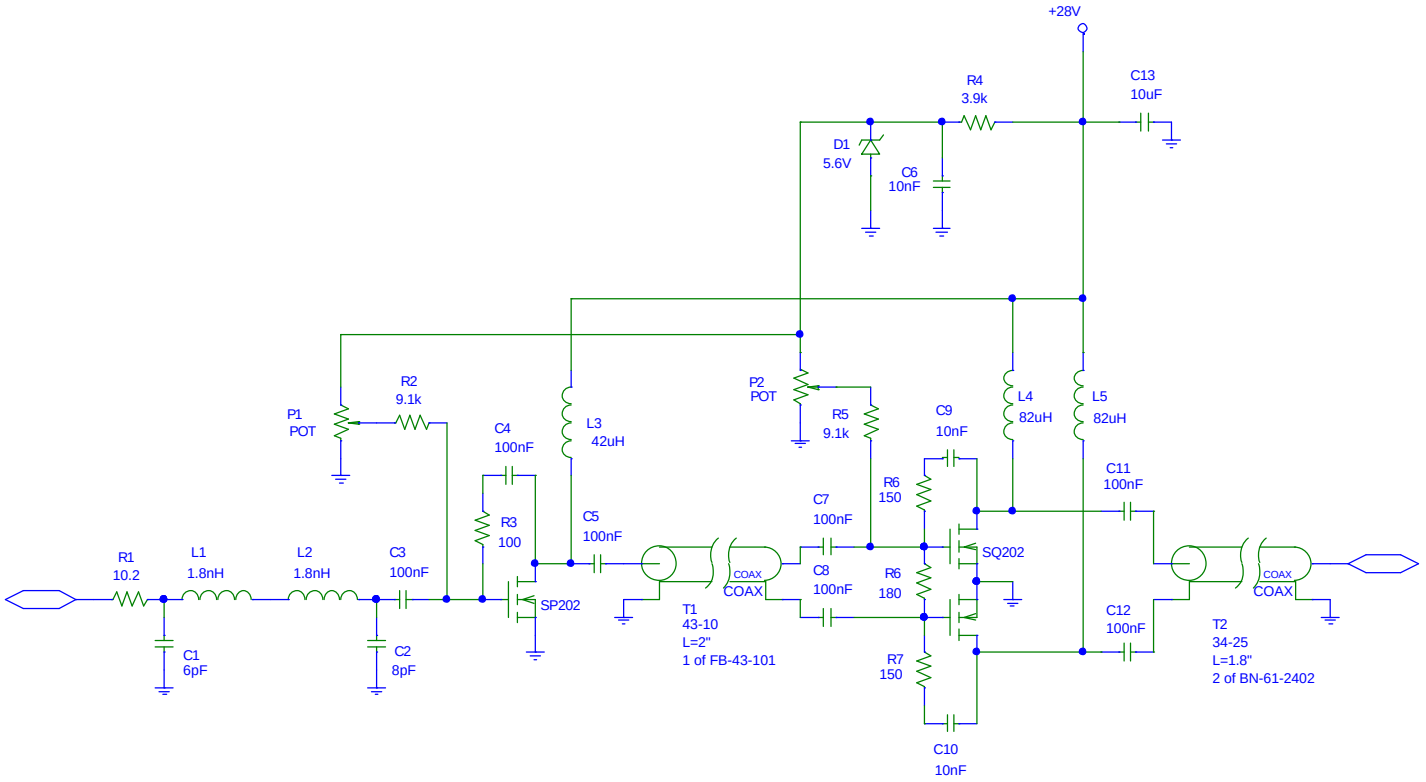
DRN BY: Cunningham	8/2/07
CHKD :	
ELECT : Cunningham	8/2/07
MECH : Cunningham	8/2/07
PROC :	
QUAL :	
PGMS :	

POLYFET RF DEVICES

TB213 SP202->SQ202 10-1000MHz 5W 20dB

SIZE	FSCM NO	Vdd=28V Idqt=0.8A	REV
			A

SCALE : 1 : 1 SHEET 1 OF 1

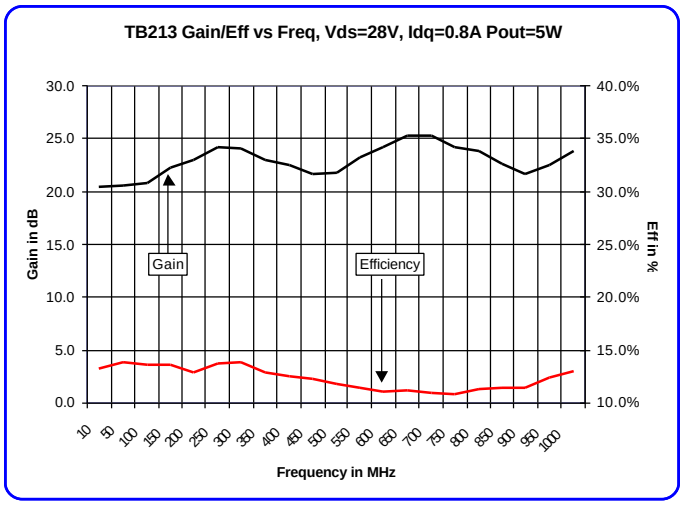


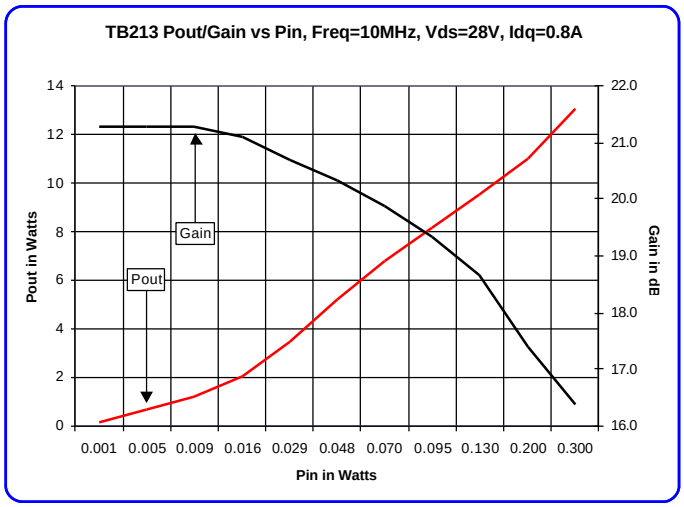
Polyfet RF Devices, Inc.
1110 Avenida Acaso
Camarillo, CA 93012
(805) 484-4210

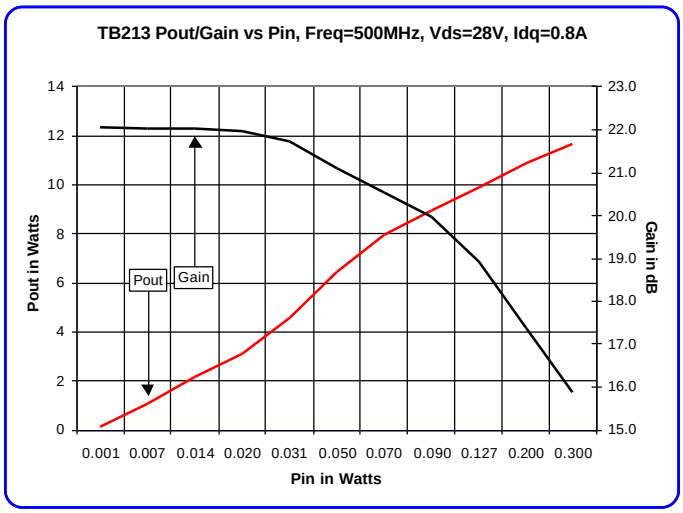
Page Size: A

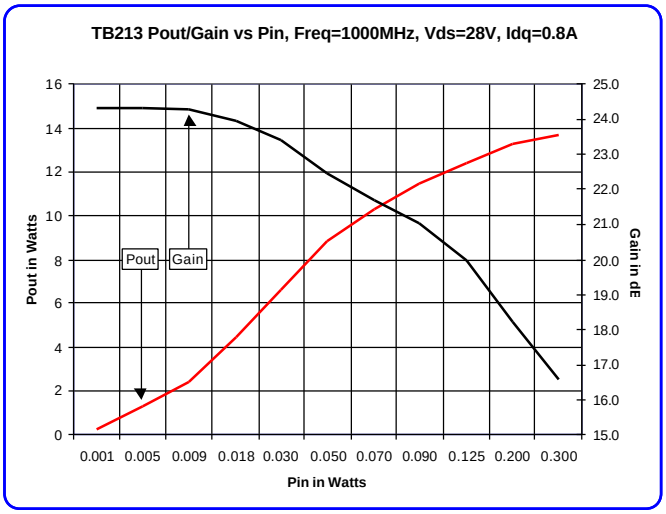
TB213, SP202->SQ202, 10MHz-1000MHz, 5W, Vds=28V, Idq=0.4A->0.4A

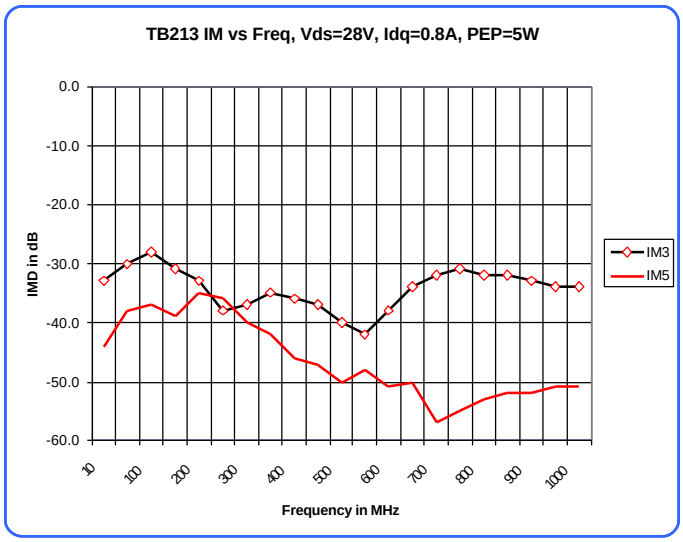
Revision: - August 13, 2007 Page 1 of 1

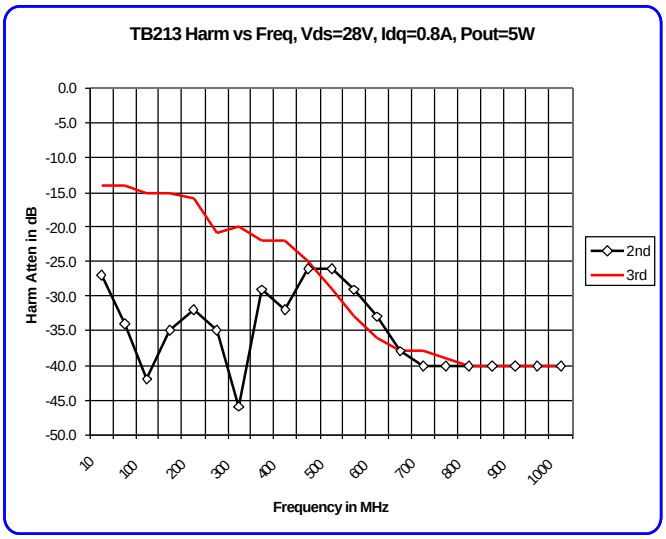

TB213 Gain/Eff vs Freq, Vds=28V, Idq=0.8A Pout=5W
Gain in dB
Eff in %
Gain
Efficiency
Frequency in MHz


TB213 Pout/Gain vs Pin, Freq=10MHz, Vds=28V, Idq=0.8A
Pout in Watts
Gain in dB
Gain
Pout
Pin in Watts


TB213 Pout/Gain vs Pin, Freq=500MHz, Vds=28V, Idq=0.8A
Pout in Watts
Gain in dB
Pout
Gain
Pin in Watts


TB213 Pout/Gain vs Pin, Freq=1000MHz, Vds=28V, Idq=0.8A
Pout in Watts
Gain in dB
Pout
Gain
Pin in Watts


TB213 IM vs Freq, Vds=28V, Idq=0.8A, PEP=5W
IMD in dB
IM3
IM5
Frequency in MHz


TB213 Harm vs Freq, Vds=28V, Idq=0.8A, Pout=5W
Harm Atten in dB
2nd
3rd
Frequency in MHz